

P-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 150	0.295 at V _{GS} = - 10 V	- 8.9 ^c	23.2 nC
	0.315 at V _{GS} = - 6.0 V	- 8.6 ^c	

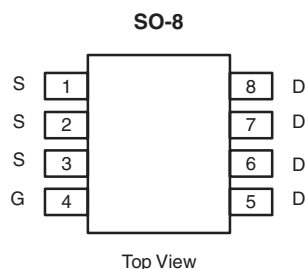
FEATURES

- TrenchFET[®] Power MOSFET
- 100% R_g Tested
- 100% UIS Tested

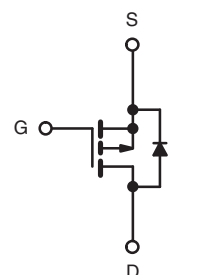

RoHS
COMPLIANT

APPLICATIONS

- Active Clamp in Intermediate DC/DC Power Supplies
- H-Bridge High Side Switch for Lighting Application



Ordering Information: Si4455DY-T1-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 150	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 2.8
		T _C = 70 °C	- 2.3
		T _A = 25 °C	- 2.0 ^{a, b}
		T _A = 70 °C	- 1.6 ^{a, b}
Pulsed Drain Current	I _{DM}	- 15	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	
Avalanche Current	I _{AS}	- 15	
Single-Pulse Avalanche Energy	E _{AS}	11.25	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	5.9
		T _C = 70 °C	3.8
		T _A = 25 °C	3.1 ^{a, b}
		T _A = 70 °C	2.0 ^{a, b}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 50 to 150	°C

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. t = 10 s.

c. Based on T_C = 25 °C.

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	$t \leq 10$ s	R_{thJA}	33	40	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Maximum under Steady State conditions is 80 °C/W.

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

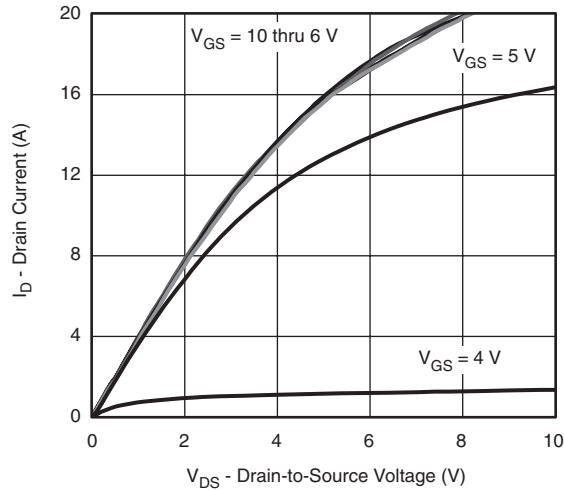
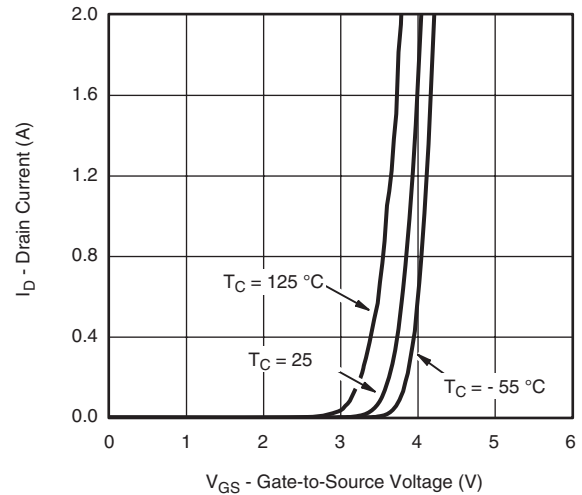
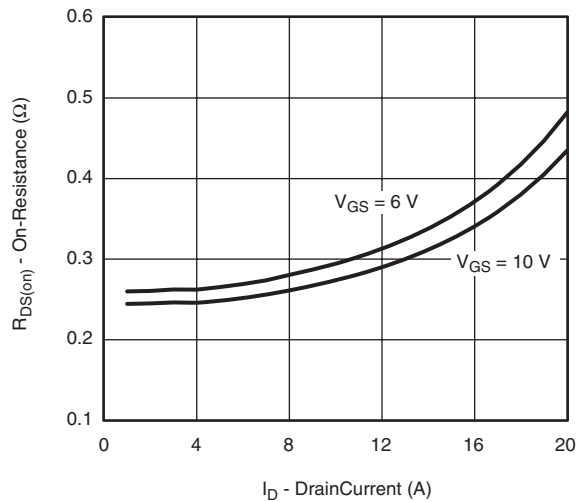
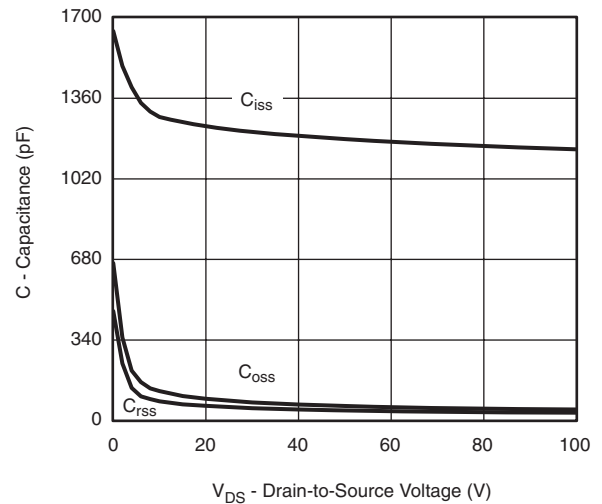
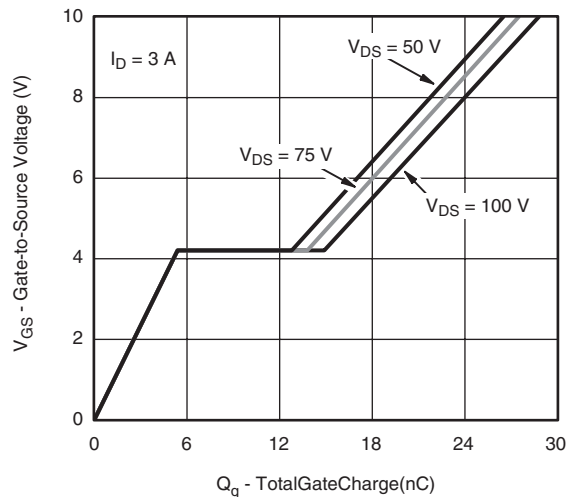
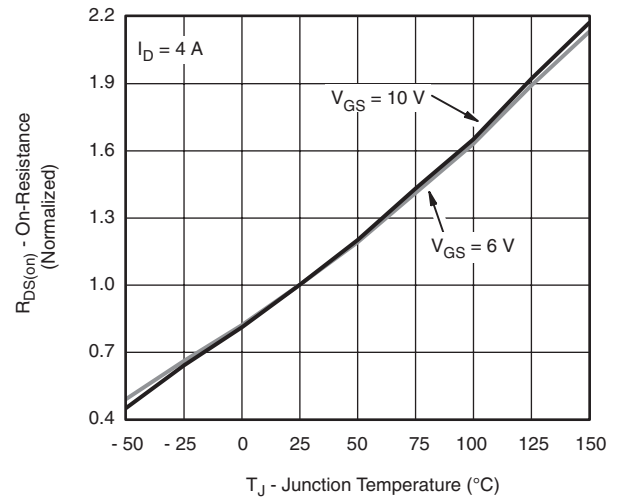
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 150			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 165		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6.6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 2		- 4	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 150 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 150 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 5 V, V _{GS} = - 10 V	- 8			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 4 A		0.245	0.295	Ω
		V _{GS} = - 6 V, I _D = - 3 A		0.260	0.315	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = 4 A		12		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 50 V, V _{GS} = 0 V, f = 1 MHz		1190		pF
Output Capacitance	C _{oss}			61		
Reverse Transfer Capacitance	C _{rss}			42		
Total Gate Charge	Q _g	V _{DS} = - 75 V, V _{GS} = - 10 V, I _D = - 3 A		27.5	42	nC
		V _{DS} = - 75 V, V _{GS} = - 6 V, I _D = - 3 A		23.2	35	
Gate-Source Charge	Q _{gs}			5.4		
Gate-Drain Charge	Q _{gd}			8.4		
Gate Resistance	R _g	f = 1 MHz		6.1	9.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 75 V, R _L = 25 Ω I _D ≅ - 3 A, V _{GEN} = - 6 V, R _g = 1 Ω		20	30	ns
Rise Time	t _r			95	145	
Turn-Off DelayTime	t _{d(off)}			38	60	
Fall Time	t _f			34	51	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 75 V, R _L = 25 Ω I _D ≅ - 3 A, V _{GEN} = - 10 V, R _g = 1 Ω		11	18	
Rise Time	t _r			28	42	
Turn-Off DelayTime	t _{d(off)}			52	78	
Fall Time	t _f			35	53	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 13	A
Pulse Diode Forward Current ^a	I _{SM}				- 15	
Body Diode Voltage	V _{SD}	I _S = - 3 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 4 A, di/dt = 100 A/μs, T _J = 25 °C		65	90	ns
Body Diode Reverse Recovery Charge	Q _{rr}			180	270	nC
Reverse Recovery Fall Time	t _a			45		ns
Reverse Recovery Rise Time	t _b			20		

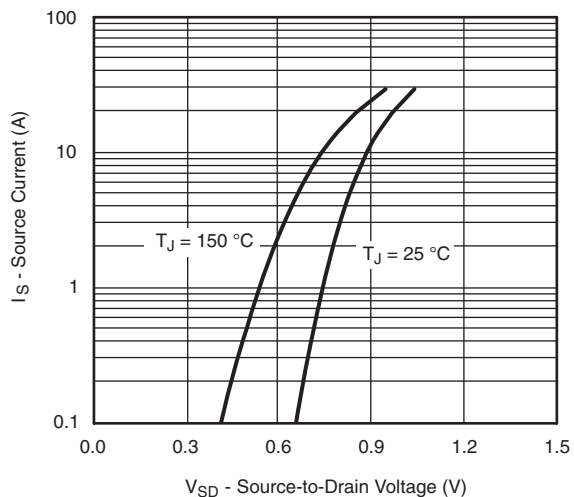
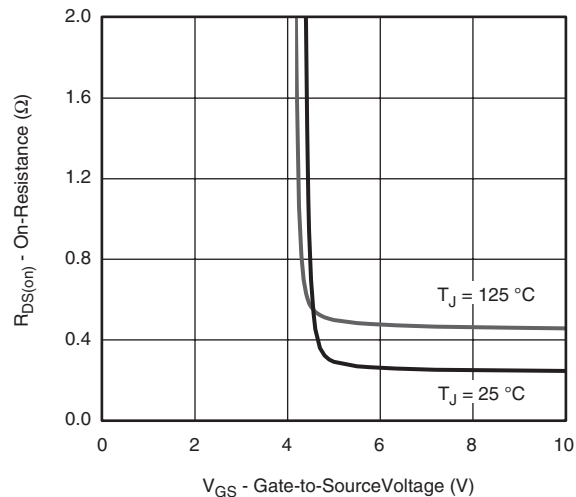
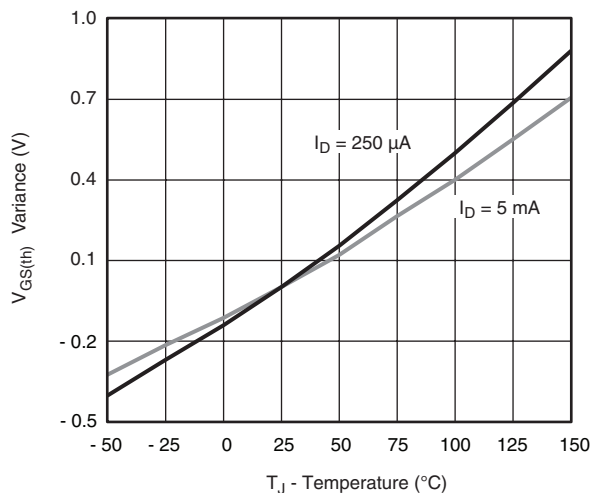
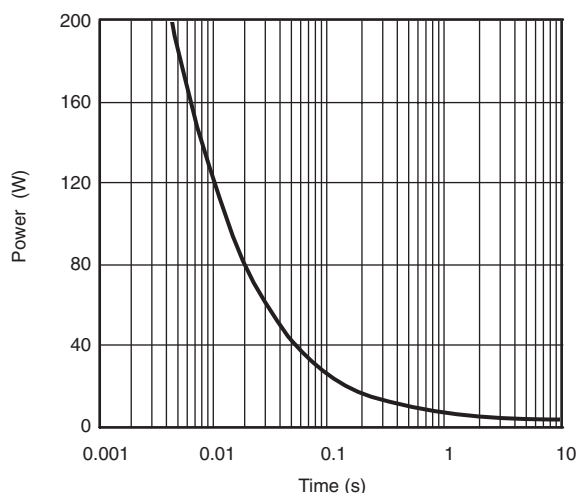
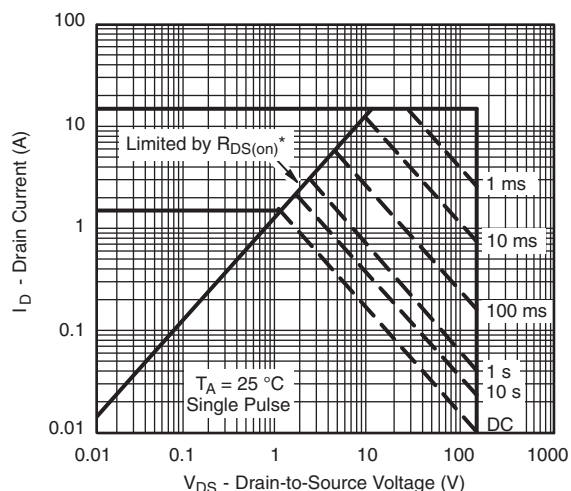
Notes:

a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.

b. Guaranteed by design, not subject to production testing.

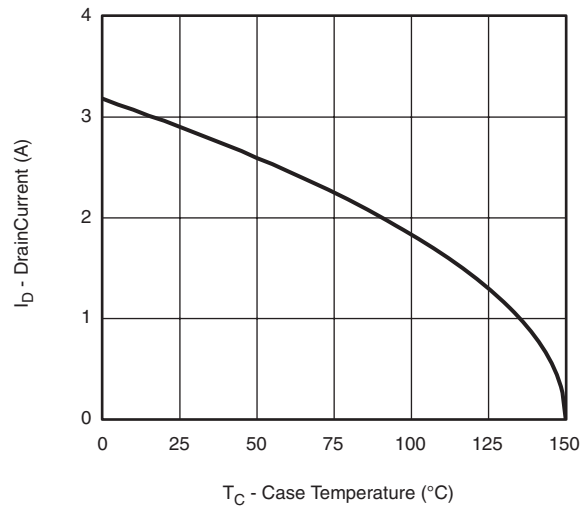
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current and Gate Voltage****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

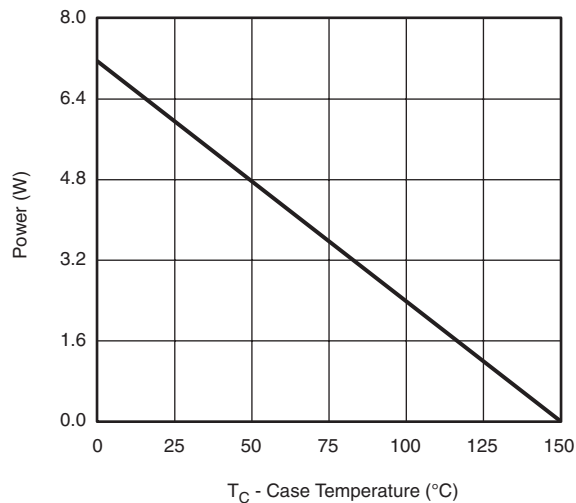
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Ambient**



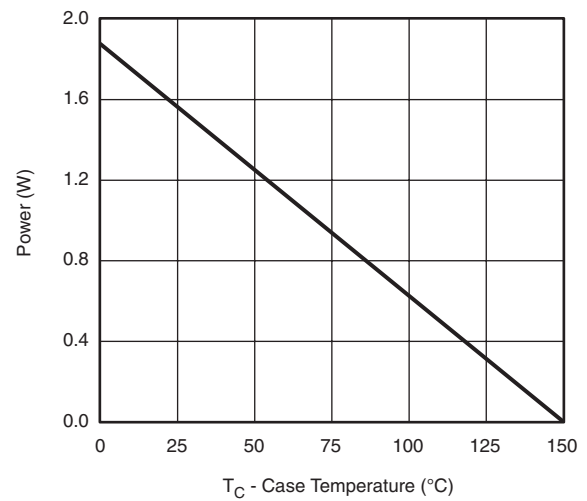
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*

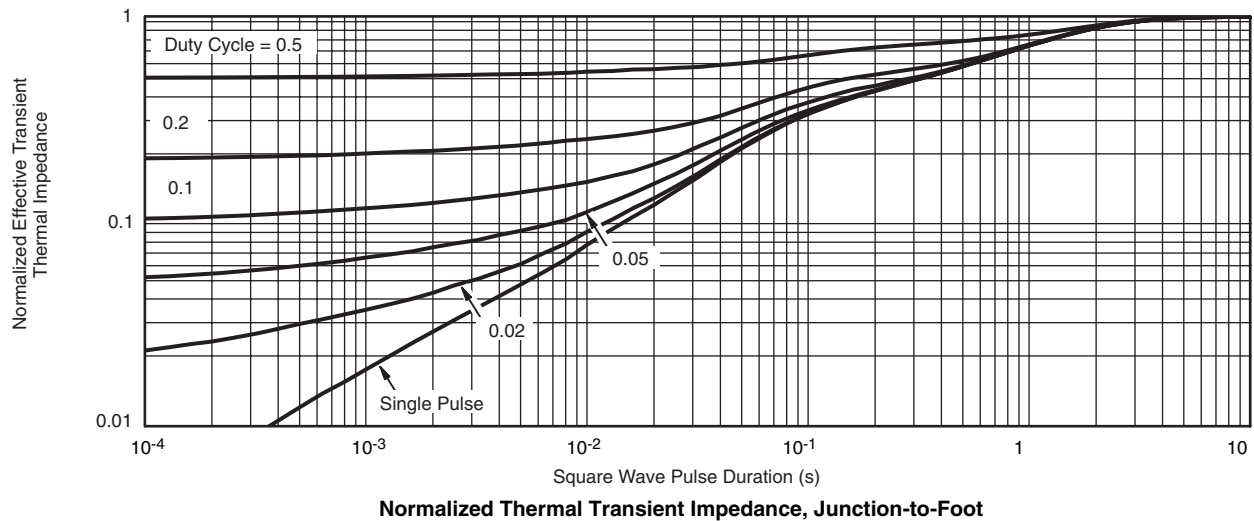
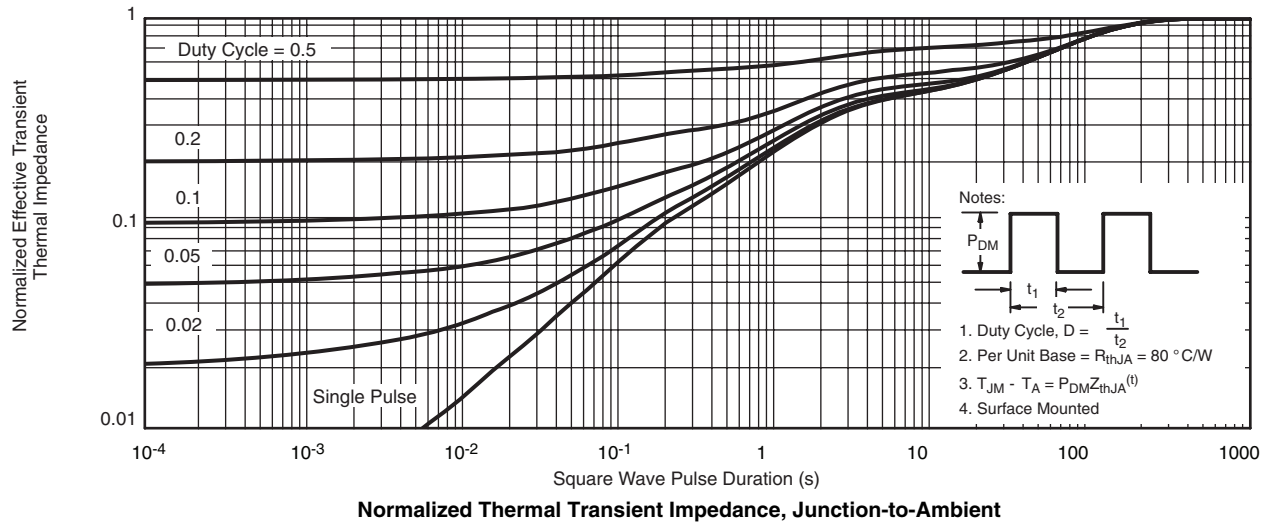


Power, Junction-to-Foot



Power, Junction-to-Ambient

* The power dissipation PD is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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